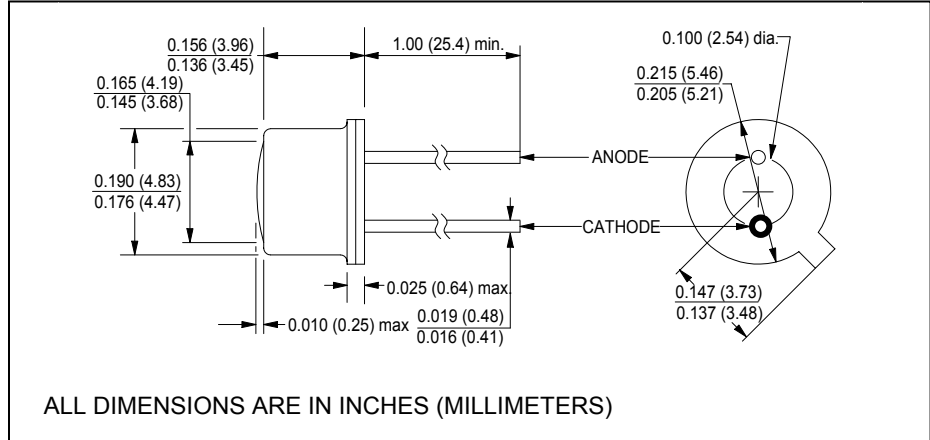
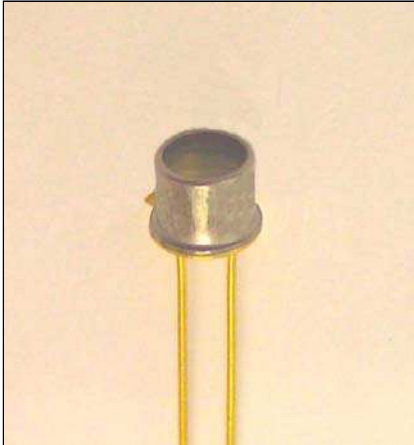


CLE331W

Aluminum Gallium Arsenide IRED Point Source Die



February, 2006



features

- 850nm wavelength
- 50MHz operation
- TO-46 hermetic package
- RoHS compliant
- Flat window can

description

The CLE331W is an advanced, high efficiency, high speed, point source, AlGaAs infrared-emitting diode intended for applications requiring a uniform output radiation pattern. The point source die junction is typically 0.002" in diameter.

absolute maximum ratings ($T_A = 25^\circ\text{C}$ unless otherwise stated)

storage temperature	-65°C to +150°C
operating temperature	-65°C to +125°C
lead soldering temperature ⁽¹⁾	260°C
continuous forward current ⁽²⁾	100mA
peak forward current (1.0ms pulse width, 10% duty cycle)	1A
reverse voltage	5V
continuous power dissipation ⁽³⁾	200mW

notes:

1. 0.06" (1.5mm) from the header for 5 seconds maximum.
2. Derate linearly 0.80mA/°C from 25°C free air temperature to $T_A = +125^\circ\text{C}$.
3. Derate linearly 1.6mW/°C from 25°C free air temperature to $T_A = +125^\circ\text{C}$.

electrical characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)						
symbol	parameter	min	typ	max	units	test conditions
P_O	Total power output	-	3.0	-	mW	$I_F = 100\text{mA}$
E_e	Irradiance ⁽⁴⁾	30	-	-	$\mu\text{W}/\text{cm}^2$	$I_F = 100\text{mA}$
λ_P	Peak emission wavelength	-	850	-	nm	$I_F = 100\text{mA}$
I_R	Reverse current	-	-	10	μA	$V_R = 3.0\text{V}$
V_F	Forward voltage	-	-	2.2	V	$I_F = 100\text{mA}$
θ_{HP}	Emission angle at half power points	-	70	-	deg.	$I_F = 100\text{mA}$
t_r, t_f	Output rise and fall time	-	5.0	10	ns	$I_F = 100\text{mA}$

notes: 4. Power/unit area measured within a 0.444" (1.128cm) diameter area, centered on the mechanical axis of the device and spaced 2.54" (6.45cm) from lens side of the tab. This is geometrically equivalent to a 10° cone.